SD Protection Diode

Low Capacitance ESD Protection Diode for High Speed Data Line

The ESD7004 surge protection is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as USB 3.0 and HDMI.

Features

- Low Capacitance (0.4 pF Typical, I/O to GND)
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Typical Applications

- USB 3.0
- HDMI
- Display Port
- eSATA

MAXIMUM RATINGS (T, I = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	TL	260	°C
IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD)	ESD ESD	±15 ±15	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note AND8308/D for further description of survivability specs.



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAM



UDFN10 CASE 517BB



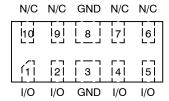
4M = Specific Device Code (tbd)

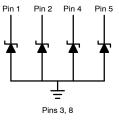
M = Date Code

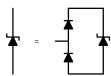
= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONFIGURATION AND SCHEMATIC







ORDERING INFORMATION

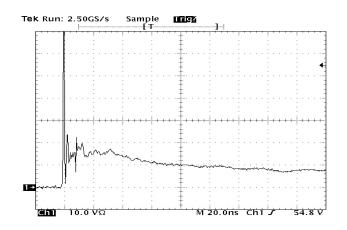
Device	Package	Shipping
ESD7004MUTAG	UDFN10 (Pb-Free)	3000 / Tape & Reel
SZESD7004MUTAG	UDFN10 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	I/O Pin to GND			5.0	V
Breakdown Voltage	V_{BR}	$I_T = 1 \text{ mA, I/O Pin to GND}$ 5.5				V
Reverse Leakage Current	I _R	V _{RWM} = 5 V, I/O Pin to GND			1.0	μΑ
Clamping Voltage (Note 1)	V _C	I _{PP} = 1 A, I/O Pin to GND (8 x 20 μs pulse)		10	V	
Clamping Voltage (Note 2)	V _C	IEC61000-4-2, ±8 KV Contact	See Figures 1 and 2		nd 2	V
Clamping Voltage V_C $I_{PP} = 8 \text{ A}$ $I_{PP} = 16 \text{ A}$ $I_{PP} = -8 \text{ A}$ $I_{PP} = -8 \text{ A}$ $I_{PP} = -16 \text{ A}$		I _{PP} = 16 A I _{PP} = -8 A		11.4 15.6 -4.5 -8.1		
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins 0.2		0.3	pF	
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins and GND 0.4		0.5	pF	

- Surge current waveform per Figure 5.
 For test procedure see Figures 3 and 4 and application note AND8307/D.
 ANSI/ESD STM5.5.1 Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 4 ns, averaging window; t₁ = 30 ns to t₂ = 60 ns.



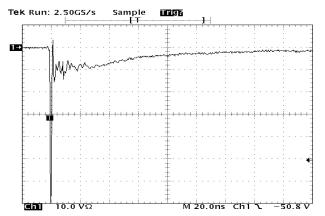


Figure 1. IEC61000-4-2 +8 KV Contact ESD **Clamping Voltage**

Figure 2. IEC61000-4-2 -8 KV Contact **Clamping Voltage**

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

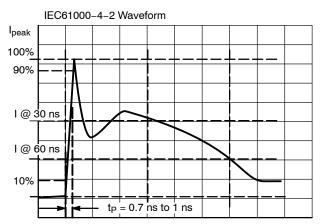


Figure 3. IEC61000-4-2 Spec

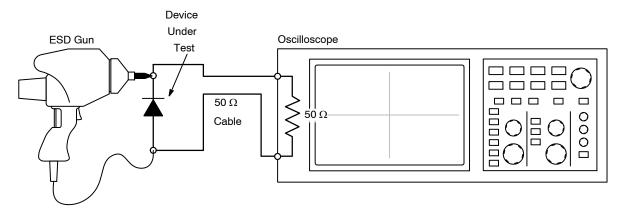


Figure 4. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

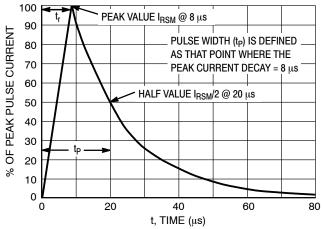
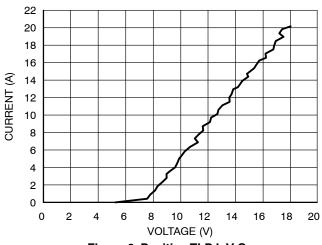


Figure 5. 8 x 20 μs Pulse Waveform





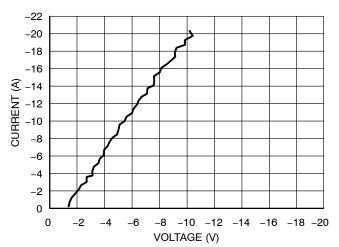


Figure 7. Negative TLP I-V Curve

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 8. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and

under 100 ns time scale match those of an ESD event. This is illustrated in Figure 9 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. A typical TLP I–V curve for the ESD7004 is shown in Figures 6 and 7.

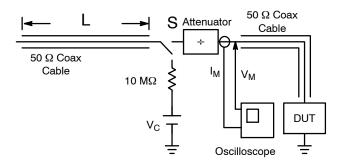


Figure 8. Simplified Schematic of a Typical TLP System

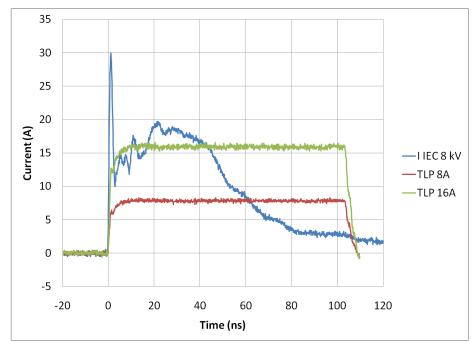
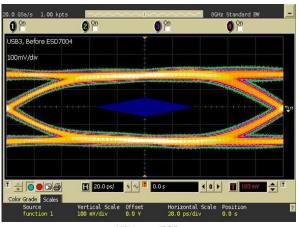
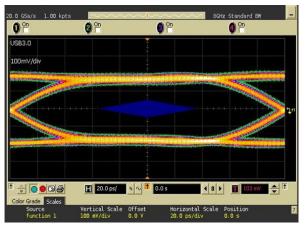


Figure 9. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

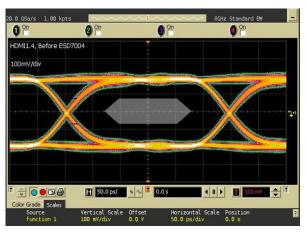


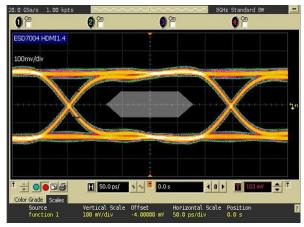


Without ESD

With ESD7004

Figure 10. USB3.0 Eye Diagram with and without ESD7004. 5.0 Gb/s, 400 mV_{PP}

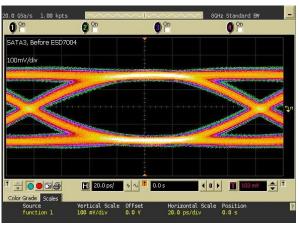


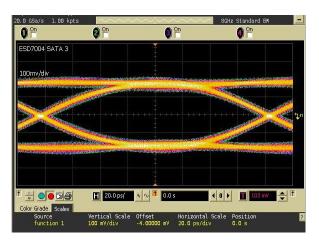


Without ESD

With ESD7004

Figure 11. HDMI1.4 Eye Diagram with and without ESD7004. 3.4 Gb/s, 400 mV_{PP}





Without ESD

With ESD7004

Figure 12. ESATA3.0 Eye Diagram with and without ESD7004. 6 Gb/s, 400 mV_{PP}

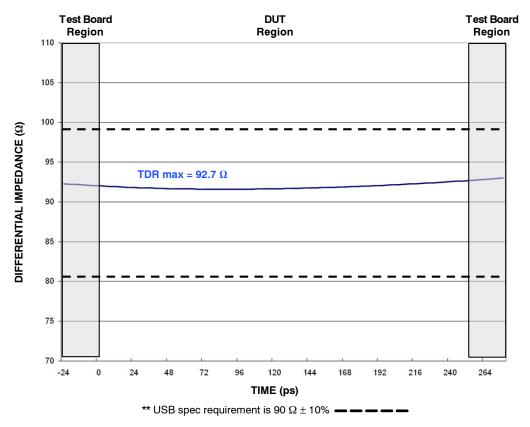


Figure 13. USB TDR Measurement. 90 Ω Differential Impedance Target, 200 ps Rise Time

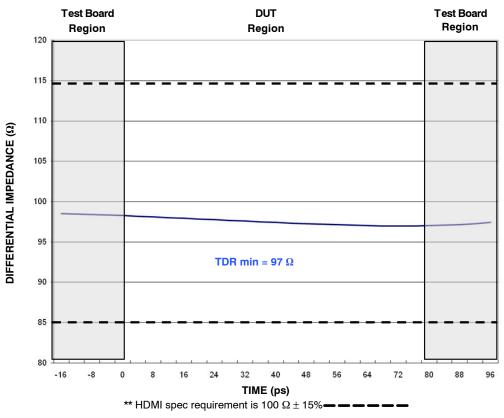


Figure 14. HDMI TDR Measurement. 100 Ω Differential Impedance Target, 200 ps Rise Time

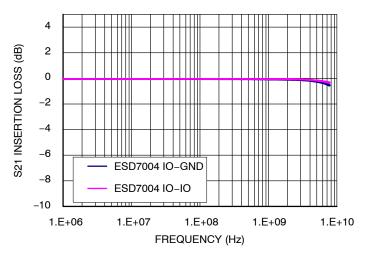


Figure 15. ESD7004 Insertion Loss

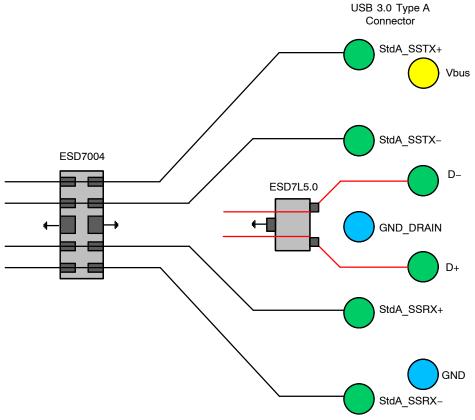


Figure 16. USB3.0 Standard A Connector Layout Diagram

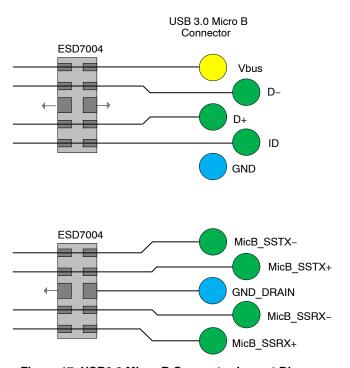


Figure 17. USB3.0 Micro B Connector Layout Diagram

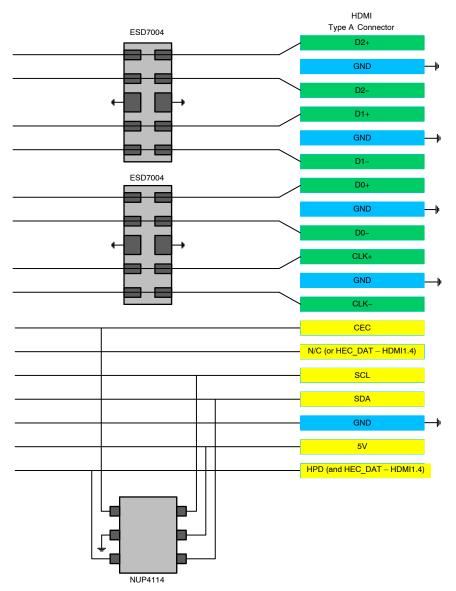


Figure 18. HDMI Layout Diagram

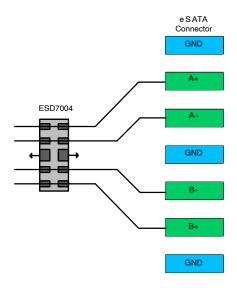


Figure 19. eSATA Layout Diagram

MECHANICAL CASE OUTLINE



UDFN10 2.5x1, 0.5P CASE 517BB-01 **ISSUE 0**

C SEATING PLANE

10X L

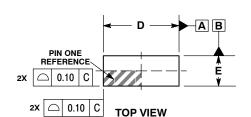
DATE 17 NOV 2009

SCALE 4:1

0.10 C

0.08 C

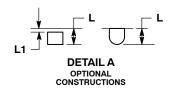
DETAIL A

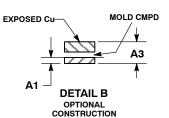


DETAIL B

SIDE VIEW

2X **b2**





NOTES:

- DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00 0.05		
A3	0.13 REF		
b	0.15	0.25	
b2	0.35	0.45	
D	2.50 BSC		
E	1.00 BSC		
е	0.50 BSC		
L	0.30 0.40		
L1	0.05		

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code М

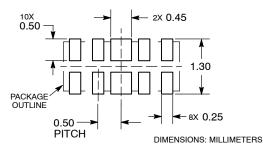
= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

8x b CAB 0.10 Ф С 0.05 NOTE 3 **BOTTOM VIEW**

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON47059E	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UDFN10 2.5X1, 0.5P		PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales